BVSS123LT1G-VB Datasheet

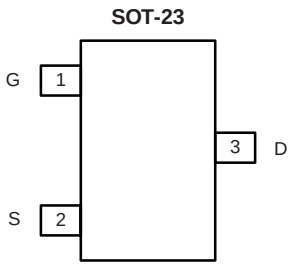
N-Channel 100-V (D-S) MOSFET

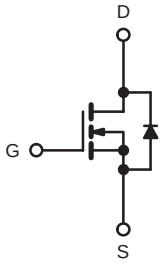
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (mA)
100	2.8 at V_{GS} = 10 V	260

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- Low Threshold: 2 V (typ.)
- Low Input Capacitance: 25 pF
- Fast Switching Speed: 25 ns
- Low Input and Output Leakage
- Trench Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 150 °C)[b]	T_A = 25 °C	I_D	260	mA
	T_A = 100 °C		150	
Pulsed Drain Current[a]		I_{DM}	800	
Power Dissipation[b]	T_A = 25 °C	P_D	0.37	W
	T_A = 100 °C		0.15	
Maximum Junction-to-Ambient[b]		R_{thJA}	350	°C/W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C

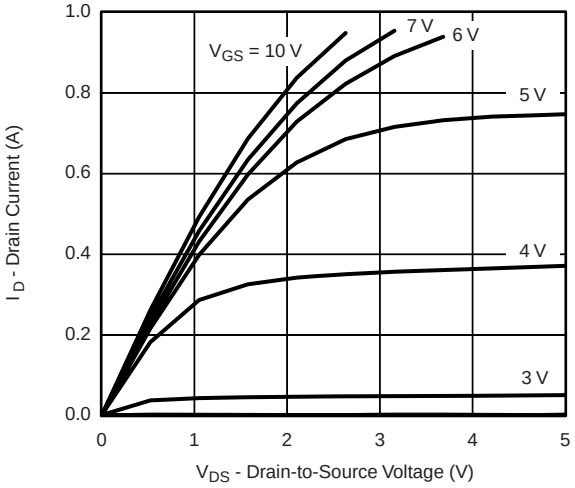
Notes:
a. Pulse width limited by maximum junction temperature.
b. Surface Mounted on FR4 board.

SPECIFICATIONS T_A = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Limits**			**Unit**
			Min.	**Typ.[a]**	**Max.**	
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 10 µA	100			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1		2.5	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 10	µA
		V_{DS} = 0 V, V_{GS} = ± 15 V			1	
		V_{DS} = 0 V, V_{GS} = ± 10 V			± 150	nA
		V_{DS} = 0 V, V_{GS} = ± 10 V, T_J = 85 °C			± 1000	
		V_{DS} = 0 V, V_{GS} = ± 5 V			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100 V, V_{GS} = 0 V			1	µA
		V_{DS} = 100V, V_{GS} = 0 V , T_J = 125 °C			500	
On-State Drain Current[a]	$I_{D(on)}$	V_{GS} = 10 V, V_{DS} = 7.5 V	500			mA
		V_{GS} = 4.5 V, V_{DS} = 10 V	300			
Drain-Source On-Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 200 mA		2.8		Ω
		V_{GS} = 4.5 V, I_D = 150 mA		3.0		
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 100 mA	100			mS
Diode Forward Voltage	V_{SD}	I_S = 100 mA, V_{GS} = 0 V			1.3	V
Dynamic[a]						
Total Gate Charge	Q_g	V_{DS} = 10 V, V_{GS} = 4.5 V $I_D \cong$ 150 mA		0.5		nC
Input Capacitance	C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V f = 1 MHz		30		pF
Output Capacitance	C_{oss}			7		
Reverse Transfer Capacitance	C_{rss}			2.0		
Switching[a, b, c]						
Turn-On Time	$t_{d(on)}$	V_{DD} = 30 V, R_L = 150 Ω $I_D \cong$ 200 mA, V_{GEN} = 10 V, R_G = 10 Ω			20	ns
Turn-Off Time	$t_{d(off)}$				30	

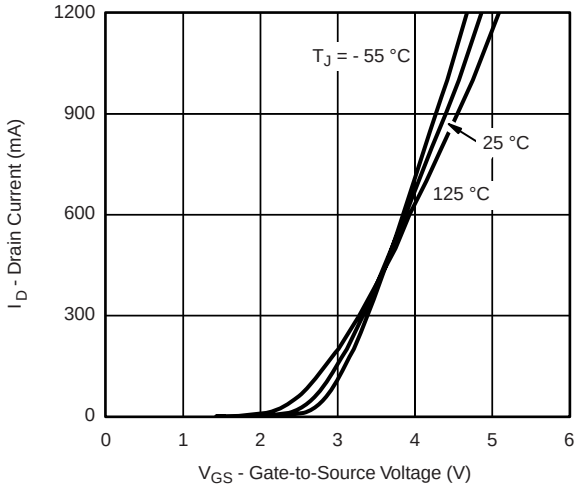
Notes:
a. For DESIGN AID ONLY, not subject to production testing.
b. Pulse test: PW ≤ 300 µs duty cycle ≤ 2 %.
c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

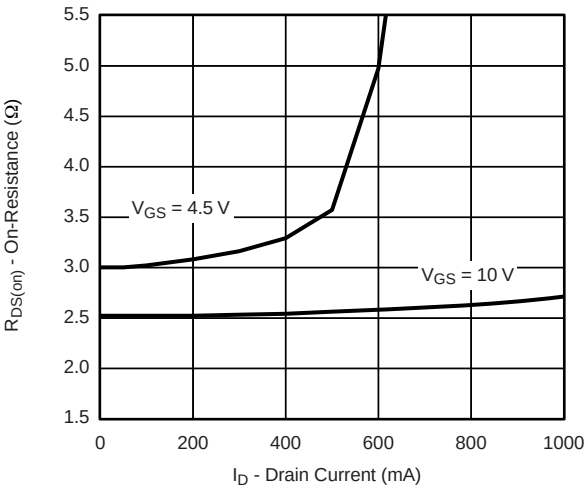
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



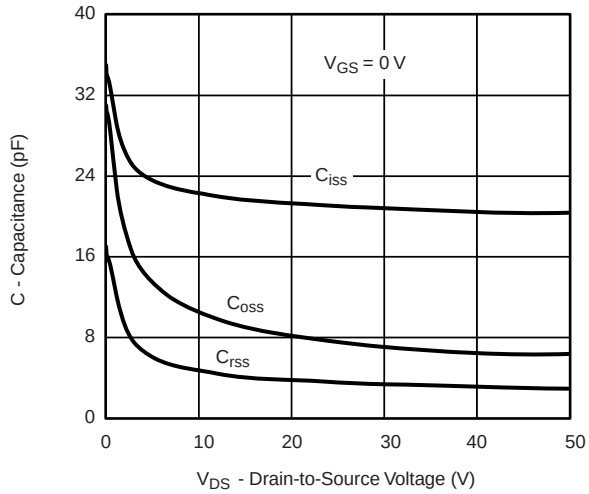
Output Characteristics



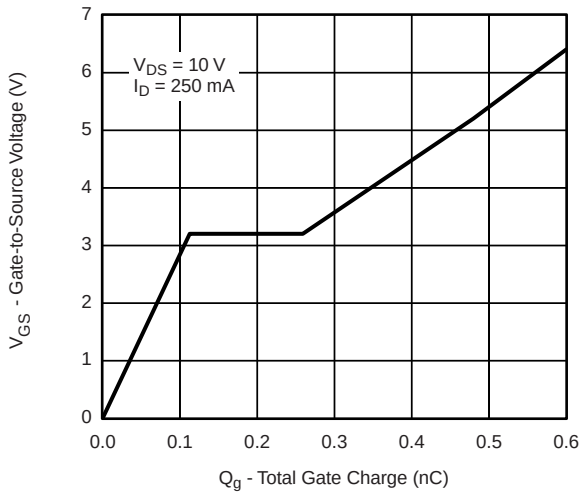
Transfer Characteristics



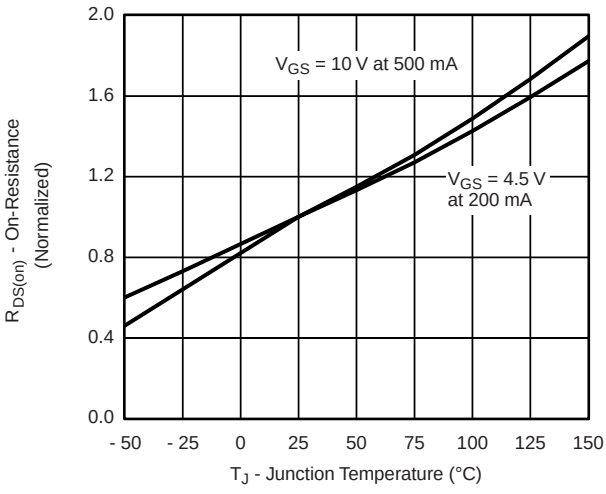
On-Resistance vs. Drain Current



Capacitance

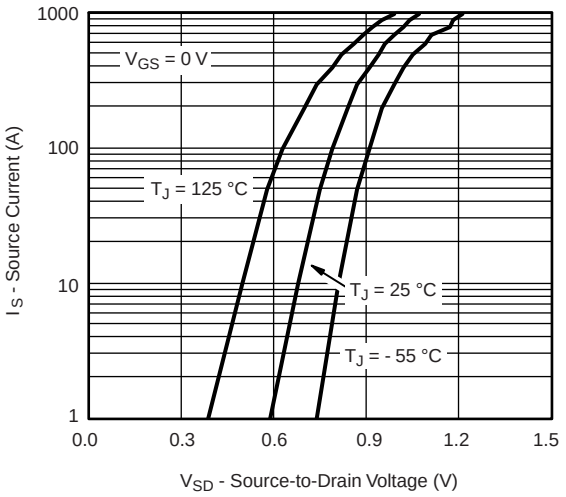


Gate Charge

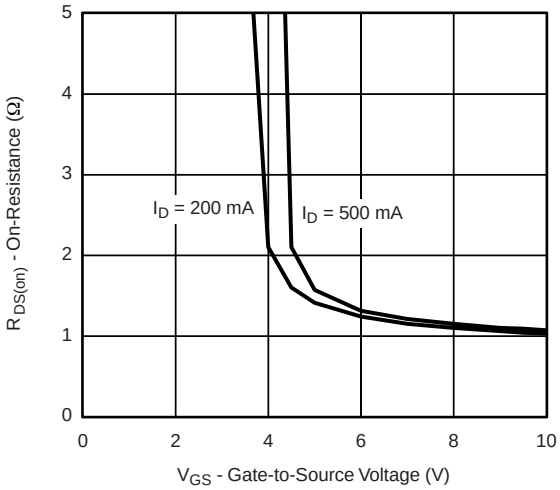


On-Resistance vs. Junction Temperature

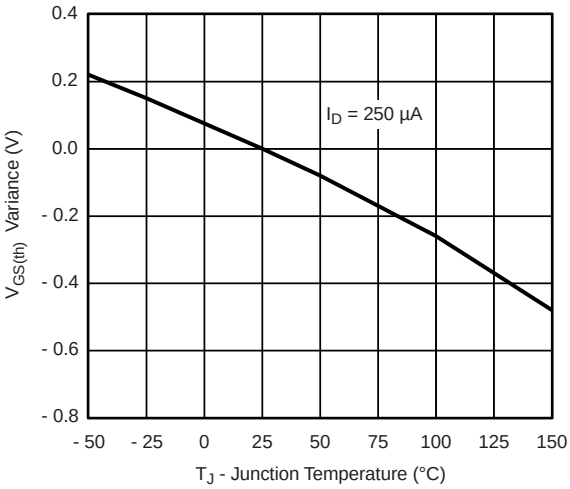
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



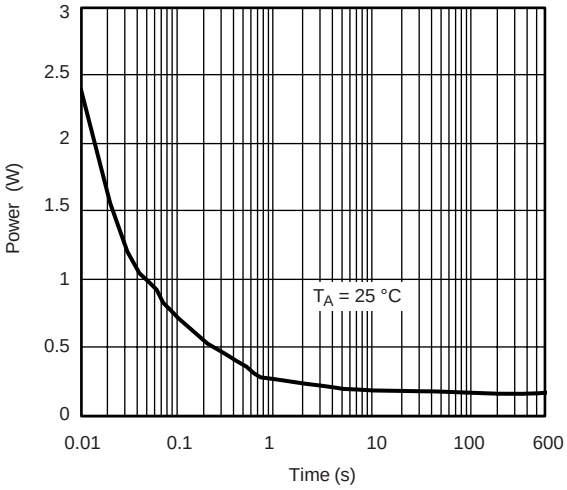
Source-Drain Diode Forward Voltage



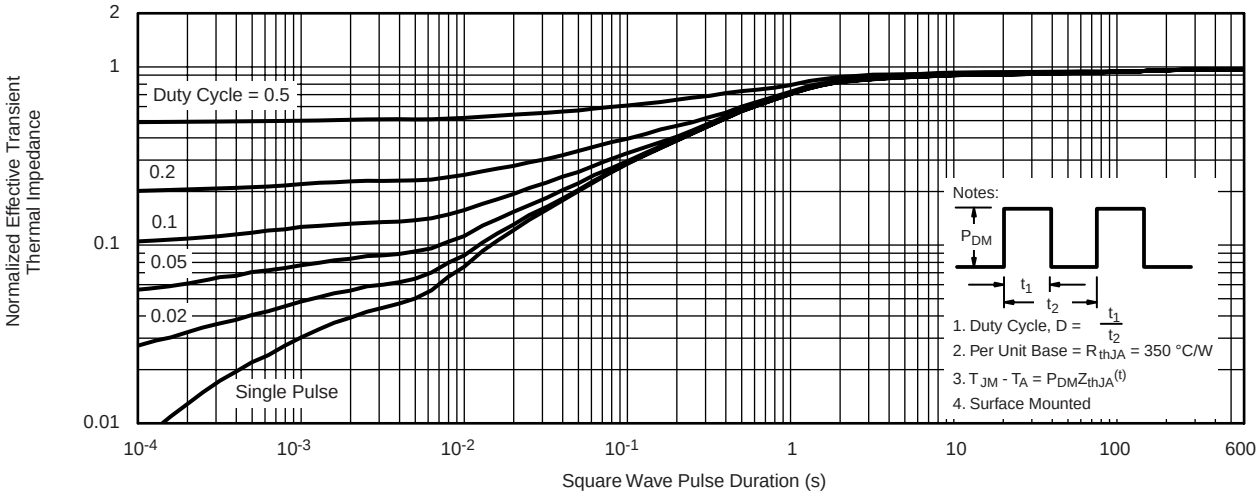
On-Resistance vs. Gate-Source Voltage



Threshold Voltage Variance Over Temperature

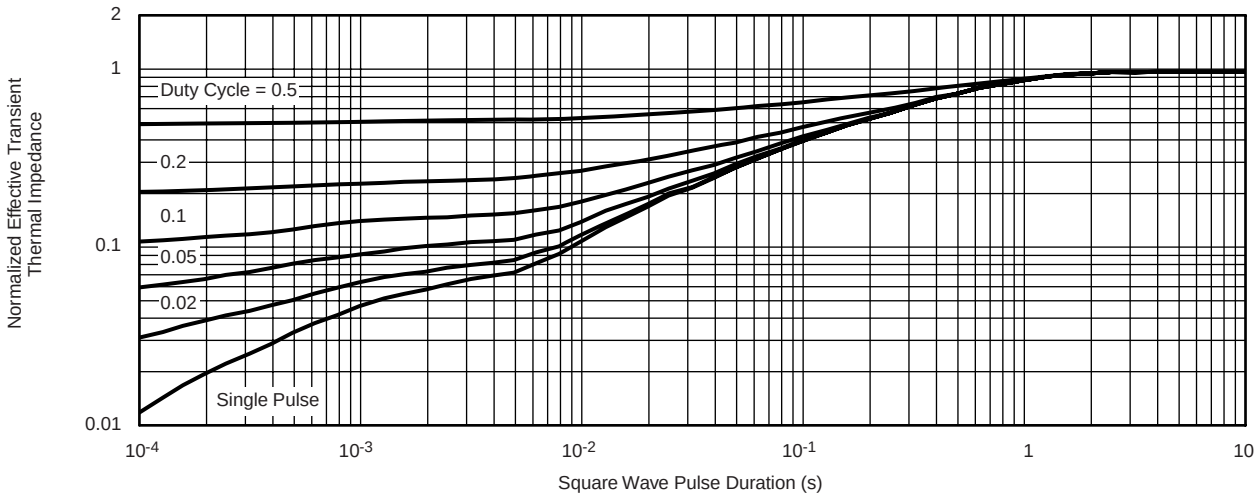


Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



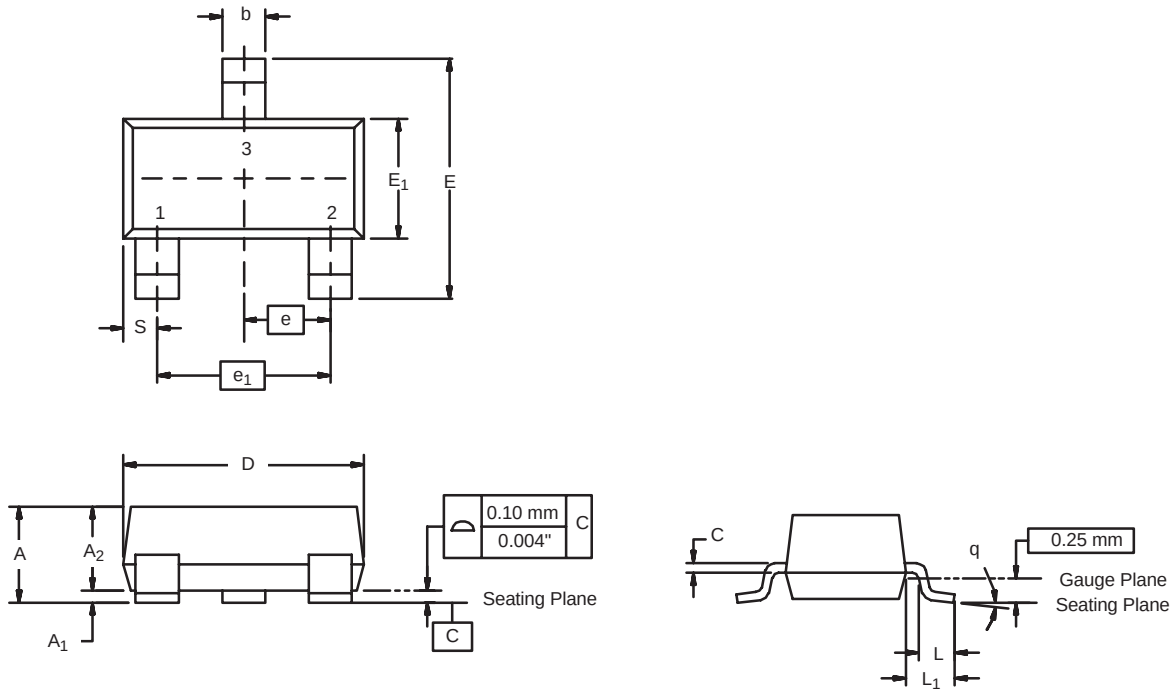
Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Foot (25 ℃)

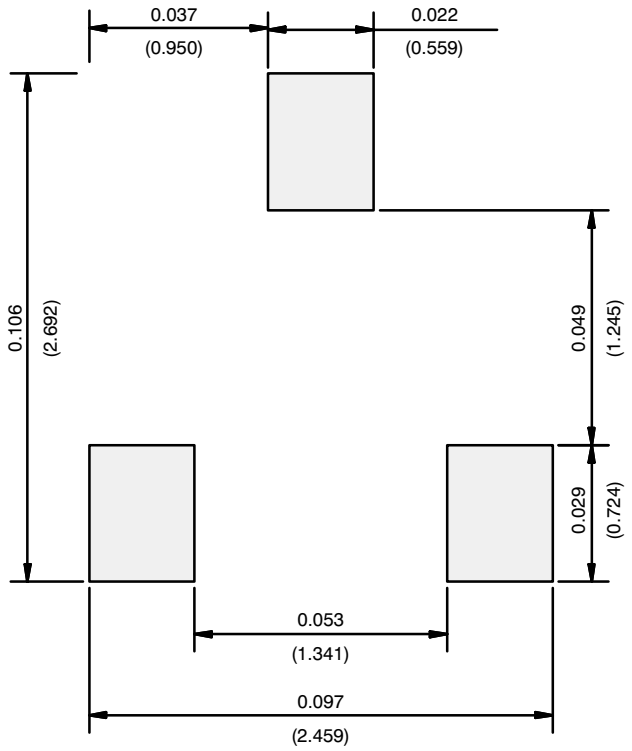
  are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A_1	0.01	0.10	0.0004	0.004
A_2	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E_1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e_1	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L_1	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°
ECN: S-03946-Rev. K, 09-Jul-01 DWG: 5479				

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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